



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089
<http://www.nteinc.com>

NTE4070B and NTE4070BT Integrated Circuit CMOS, Quad Exclusive OR Gate

Description:

The NTE4070B (14-Lead DIP) and NTE4070BT (SOIC-14) are quad exclusive OR gates constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired.

Features:

- Quiescent Current = 0.5nA Typ/Pkg at 5 Vdc
- Noise Immunity = 45% of V_{DD} (Typ)
- Supply Voltage Range = 3Vdc to 18Vdc
- All Outputs Buffered
- Capable of Driving Two Low-Power TTL Loads, One Low-Power Schottky TTL Load or Two HTL Loads Over the Rated Temperature Range
- Double Diode Protection on All Inputs

Absolute Maximum Ratings: (Voltages Referenced to V_{SS}, Note 1)

DC Supply Voltage, V _{DD}	-0.5 to +18.0V
Input Voltage (All Inputs), V _{in}	-0.5 to V _{DD} + 0.5V
DC Current Drain (Per Pin), I	10mA
Operating Temperature Range, T _{sA}	-55 to +125°C
Storage Temperature Range, T _{stg}	-65 to +150°C
Lead Temperature (8-Seconds Soldering), T _L	260°C

Note 1. These devices contain circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. For proper operation it is recommended that V_{in} and V_{out} be constrained to the range V_{SS} ≤ (V_{in} or V_{out}) ≤ V_{DD}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}).

Electrical Characteristics: (Voltages referenced to V_{SS} , Note 2)

Parameter	Symbol	V_{DD} Vdc	-55°C		+25°C			+125°C		Unit
			Min	Max	Min	Typ	Max	Min	Max	
Output Voltage "0" Level $V_{in} = V_{DD}$ or 0 "1" Level $V_{in} = 0$ or V_{DD}	V_{OL}	5.0	-	0.05	-	0	0.05	-	0.05	Vdc
		10	-	0.05	-	0	0.05	-	0.05	Vdc
		15	-	0.05	-	0	0.05	-	0.05	Vdc
	V_{OH}	5.0	4.95	-	4.95	5.0	-	4.95	-	Vdc
		10	9.95	-	9.95	10	-	9.95	-	Vdc
		15	14.95	-	14.95	15	-	14.95	-	Vdc
Input Voltage "0" Level ($V_O = 4.5$ or 0.5 Vdc) ($V_O = 9.0$ or 1.0 Vdc) ($V_O = 13.5$ or 1.5 Vdc) "1" Level ($V_O = 0.5$ or 4.5 Vdc) ($V_O = 1.0$ or 9.0 Vdc) ($V_O = 1.5$ or 13.5 Vdc)	V_{IL}	5.0	-	1.5	-	2.25	1.5	-	1.5	Vdc
		10	-	3.0	-	4.50	3.0	-	3.0	Vdc
		15	-	4.0	-	6.75	4.0	-	4.0	Vdc
	V_{IH}	5.0	3.5	-	3.5	2.75	-	3.5	-	Vdc
		10	7.0	-	7.0	5.50	-	7.0	-	Vdc
		15	11.0	-	11.0	8.25	-	11.0	-	Vdc
Output Drive Current Source ($V_{OH} = 2.5$ Vdc) ($V_{OH} = 4.6$ Vdc) ($V_{OH} = 9.5$ Vdc) ($V_{OH} = 13.5$ Vdc) Sink ($V_{OL} = 0.4$ Vdc) ($V_{OL} = 0.5$ Vdc) ($V_{OL} = 1.5$ Vdc)	I_{OH}	5.0	-3.0	-	-2.4	-4.2	-	-1.7	-	mAdc
		5.0	-0.64	-	-0.51	-0.88	-	-0.36	-	mAdc
		10	-1.6	-	-1.3	-2.25	-	-0.9	-	mAdc
		15	-4.2	-	-3.4	-8.8	-	-2.4	-	mAdc
	I_{OL}	5.0	0.64	-	0.51	0.88	-	0.36	-	mAdc
		10	1.6	-	1.3	2.25	-	0.9	-	mAdc
		15	4.2	-	3.4	8.8	-	2.4	-	mAdc
Input Current	I_{in}	15	-	± 0.1	-	± 0.00001	± 0.1	-	± 0.1	μ Adc
Input Capacitance ($V_{IN} = 0$)	C_{in}	-	-	-	-	5.0	7.5	-	-	pF
Quiescent Current (Per Package)	I_{DD}	5.0	-	0.25	-	0.0005	0.25	-	7.5	μ Adc
		10	-	0.5	-	0.0010	0.5	-	15	μ Adc
		15	-	1.0	-	0.0015	1.0	-	30	μ Adc
Total Supply Current (Dynamic plus Quiescent, Per Package, $C_L = 50$ pF on all outputs, all buffers switching, Note 3, Note 4)	I_T	5.0	$I_T = (0.3\mu A/kHz) f + I_{DD}$							μ Adc
		10	$I_T = (0.6\mu A/kHz) f + I_{DD}$							μ Adc
		15	$I_T = (0.8\mu A/kHz) f + I_{DD}$							μ Adc

Note 2. Data labeled "Typ" is not to be used for design purposes but is intended as an indication of the device's potential performance.

Note 3. The formulas given are for the typical characteristics only at +25°C.

Note 4. To calculate total supply current at loads other than 50pF:

$$I_T(C_L) = I_T(50pF) + 1 \times 10^{-3}(C_L - 50) V_{DD}f$$

where: I_T is in μA (per package), C_L in pF, V_{DD} in volts and f in kHz is input frequency.

Note 3. The formulas given are for the typical characteristics only at +25°C.

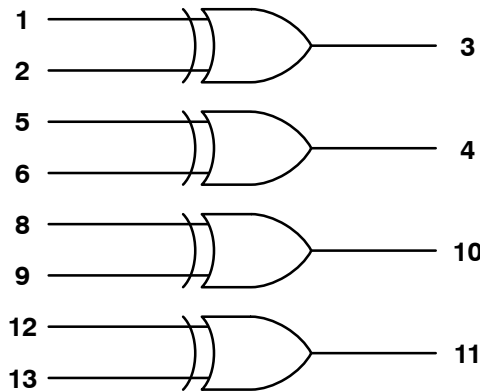
Switching Characteristics: ($C_L = 50\text{pF}$, $T_A = +25^\circ\text{C}$, Note 2)

Parameter	Symbol	V_{DD} Vdc	Min	Typ	Max	Unit
Output Rise and Fall Times $t_{TLH}, t_{THL} = (1.35\text{ns/pf}) C_L + 33\text{ns}$ $t_{TLH}, t_{THL} = (0.60\text{ns/pf}) C_L + 20\text{ns}$ $t_{TLH}, t_{THL} = (0.40\text{ns/pf}) C_L + 20\text{ns}$	t_{TLH}, t_{THL}	5.0	-	100	200	ns
		10	-	50	100	ns
		15	-	40	80	ns
Propagation Delay Time $t_{PLH}, t_{PHL} = (0.90\text{ns/pf}) C_L + 115\text{ns}$ $t_{PLH}, t_{PHL} = (0.36\text{ns/pf}) C_L + 47\text{ns}$ $t_{PLH}, t_{PHL} = (0.26\text{ns/pf}) C_L + 37\text{ns}$	t_{PLH}, t_{PHL}	5.0	-	175	350	ns
		10	-	75	150	ns
		15	-	50	100	ns

Note 2. Data labeled “Typ” is not to be used for design purposes but is intended as an indication of the device’s potential performance.

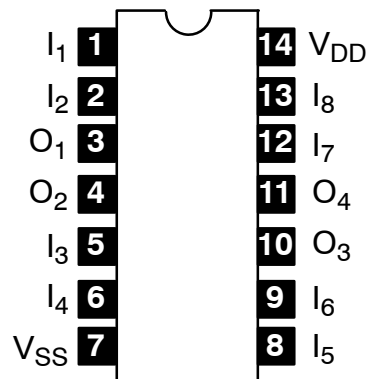
Note 3. The formulas given are for the typical characteristics only at $+25^\circ\text{C}$.

Logic Diagram

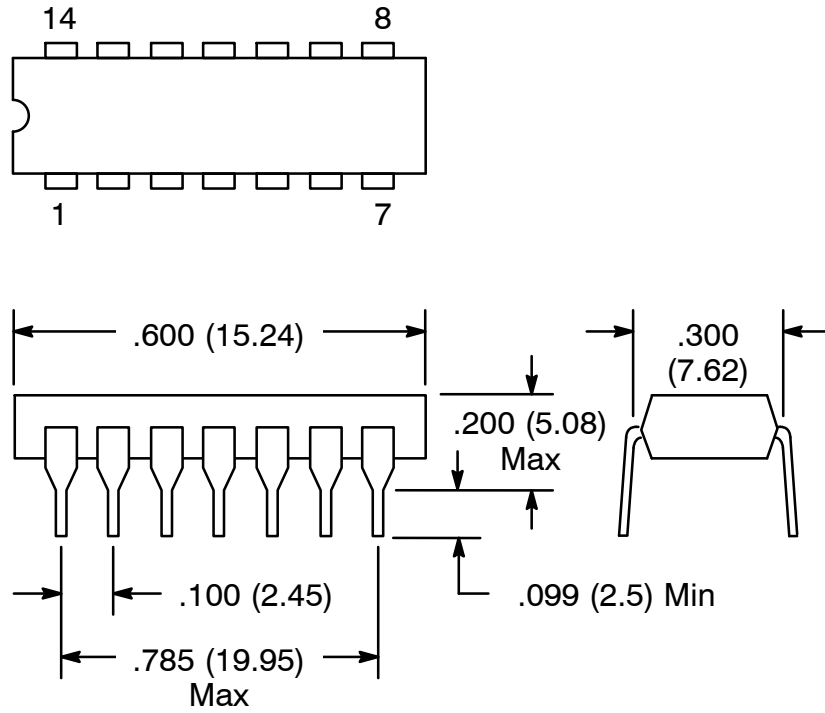


$V_{DD} = \text{Pin14}$
 $V_{SS} = \text{Pin7}$

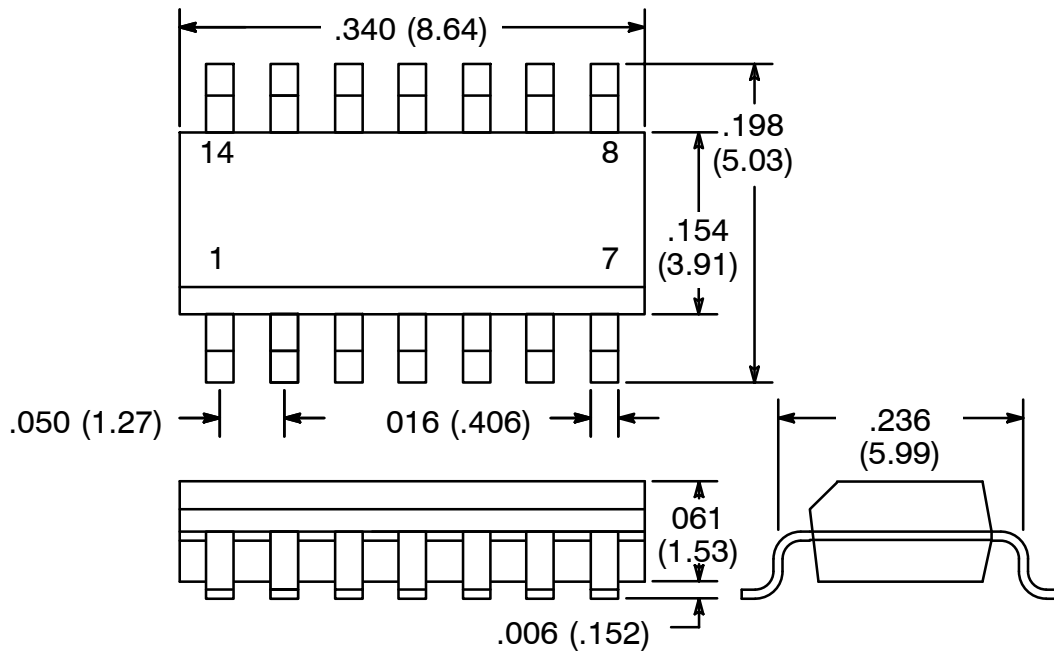
Pin Connection Diagram



NTE4070B



NTE4070BT



NOTE: Pin1 on Beveled Edge